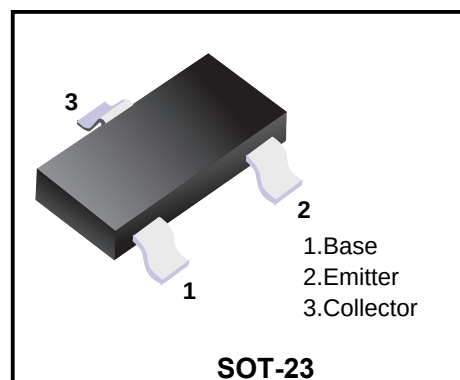


NPN Transistors

Features

- High DC Current gain.
- Complimentary to 2SB624



Absolute Maximum Ratings (Ta=25℃)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	30	V
Collector - Emitter Voltage	V _{CEO}	25	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _c	700	mA
Collector Power Dissipation	P _c	200	mW
Junction Temperature	T _J	150	℃
Storage Temperature Range	T _{stg}	-55 to 150	

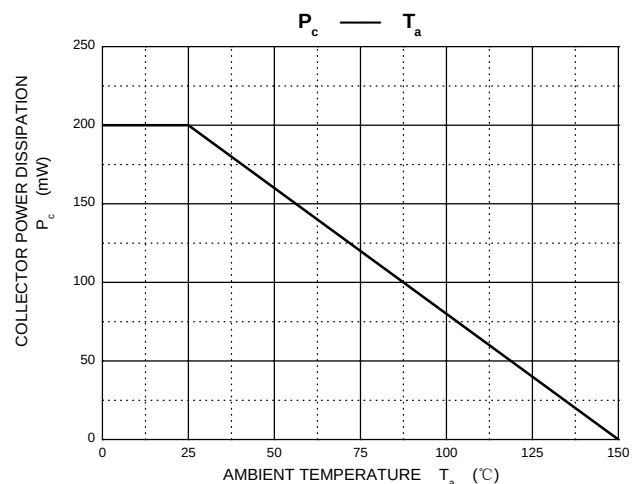
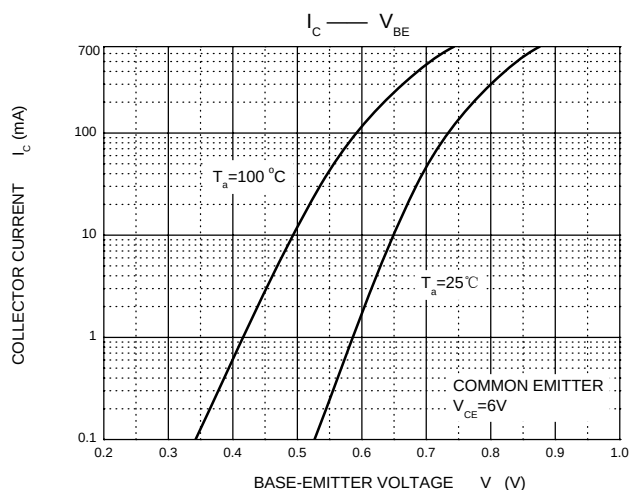
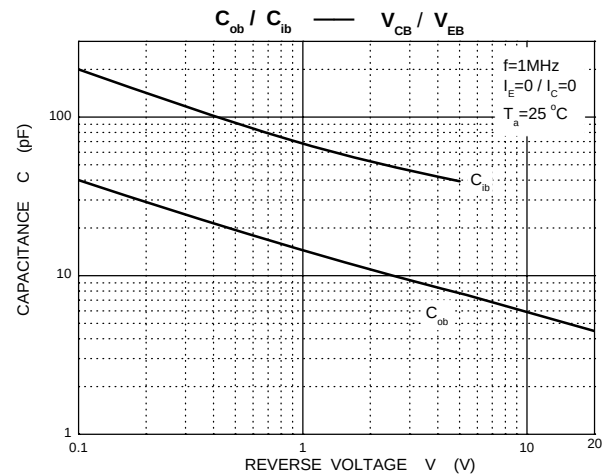
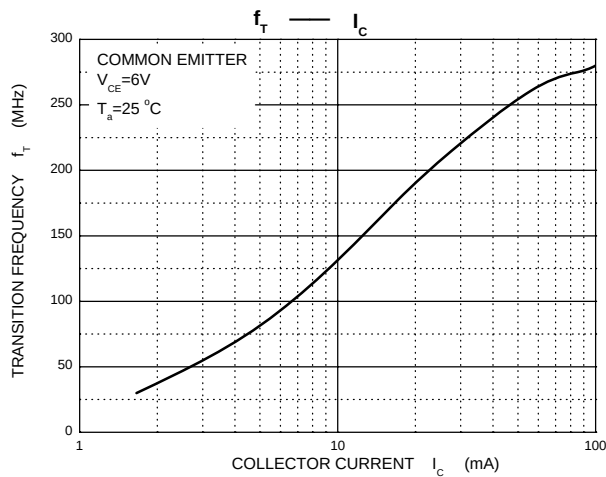
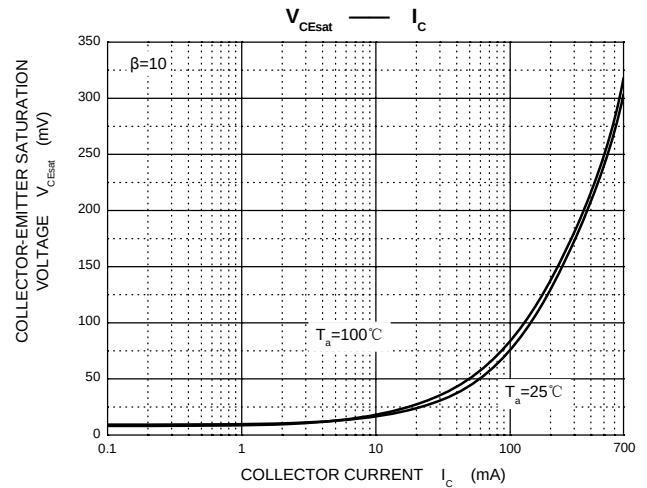
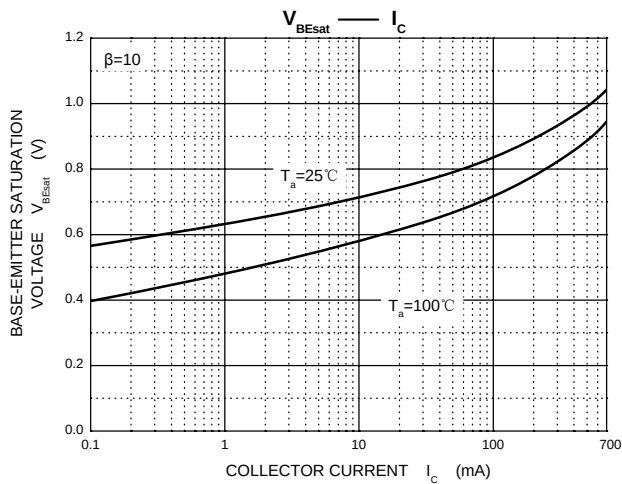
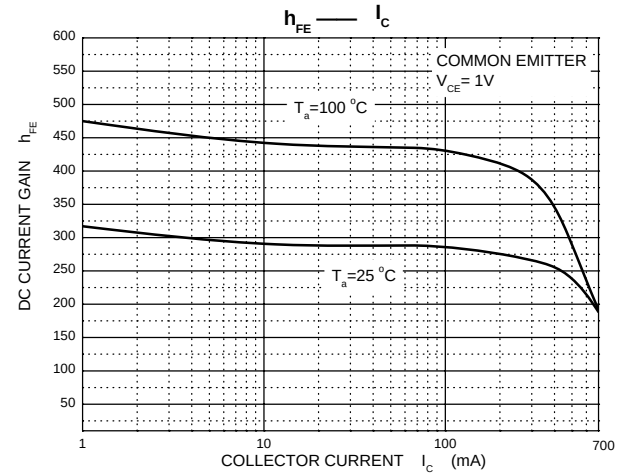
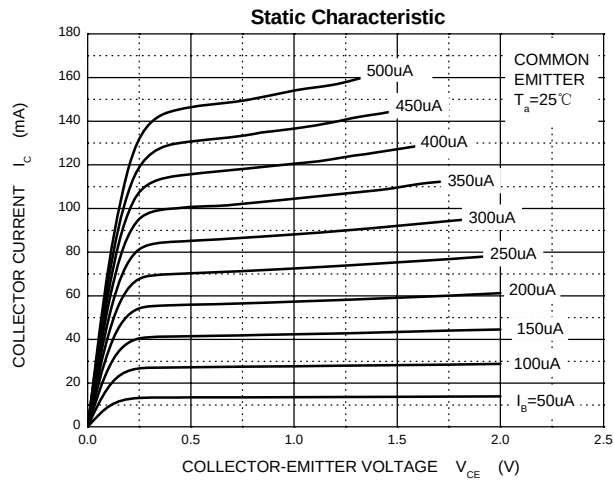
Electrical Characteristics (Ta=25℃ unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 100 μA, I _E = 0	30			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 1 mA, I _B = 0	25			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _c = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 30 V, I _E = 0			100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _c =0			100	
Collector-emitter saturation voltage (Note.1)	V _{CE(sat)}	I _c =700 mA, I _B =70mA			0.6	V
Base - emitter saturation voltage (Note.1)	V _{BE(sat)}	I _c =700 mA, I _B =70mA			1.2	
Base - emitter voltage (Note.1)	V _{BE}	V _{CE} = 6V, I _c = 10mA	0.6		0.7	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = 1V, I _c = 100mA	110		400	
	h _{FE(2)}	V _{CE} = 1V, I _c = 700mA	50			
Collector output capacitance	C _{ob}	V _{CB} = 6V, I _E = 10mA, f=10MHz		12		pF
Transition frequency	f _T	V _{CE} = 6V, I _c = 10mA	170			MHz

Note.1: Pulse test : Pulse width ≤350μs,Duty Cycle≤2%.

h_{FE} Classification

Type	2SD596-DV1	2SD596-DV2	2SD596-DV3	2SD596-DV4	2SD596-DV5
Range	110-180	135-220	170-270	200-320	250-400
Marking	DV1	DV2	DV3	DV4	DV5



Ordering information

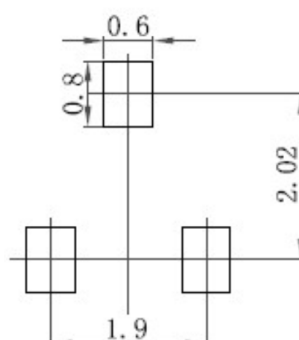
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



Disclaimer

The information presented in this document is for reference only. Guangdong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.